

First-Principles Investigation of NH₃ Adsorption and Sensing Behavior on Cu-Doped MoSe₂ Monolayer

ARUNIMA RAJ PANDEY¹, S N JAISWAL^{2*}, ANIL KUMAR CHAUDHARY³

^{1, 2, 3}Department of Electronics and Communication Engineering, BIT, Gorakhpur (U.P.), India

*Corresponding Author: Dr. S. N. Jaiswal

Abstract- In this work, we use first-principles calculations to examine the potential of copper (Cu)-doped two-dimensional (2D) MoSe₂ monolayer for NH₃ capture. Cu-doped MoSe₂ electronic properties in the context of NH₃ sensing have been comprehensively investigated using Density Functional Theory (DFT). The negative formation and binding energy of -6.62 and -4.78 eV show the electronic stability of undoped Cu-doped MoSe₂ ML. Band structure, sensitivity, recovery time, charge transfer, and adsorption energy of SO₂ molecules on the doped monolayer are all examined. Following NH₃ adsorption, the results show significant alterations in the electronic and sensing properties of Cu-doped MoSe₂, highlighting its potential as a reliable and effective material for gas sensing applications.

Keywords: Adsorption, MoSe₂ monolayer, Bandgap

I. INTRODUCTION

Air pollution is one of the most critical environmental challenges threatening human health and ecological systems worldwide. The rapid expansion of industrial, agricultural, and urban activities has significantly increased emissions of toxic and hazardous gases into the atmosphere [1]. Among these pollutants, Ammonia (NH₃) is a highly toxic and volatile gas widely used in agriculture, refrigeration, chemical synthesis, and industrial processes [2]. Even at low concentrations, prolonged exposure can cause severe respiratory irritation, eye damage, and environmental pollution [3]. Due to the serious risks of ammonia exposure, real-time, reliable, and highly sensitive detection systems are urgently needed for industrial safety, environmental monitoring, and public health. Given these requirements, 2D nanomaterials stand out as ideal candidates for advanced gas sensors thanks to their large surface area, fast electron transport, and high sensitivity to surface interactions [4]. Unlike thicker materials, 2D structures expose all reactive sites directly to gases, causing clear changes in

electrical behavior when molecules adsorb [5]. Among various materials, MoSe₂ has shown heightened reactivity when exposed to air, indicating strong interactions with atmospheric components. This makes MoSe₂ a promising candidate for applications in energy storage, optoelectronics, and gas sensing technologies [6]. Furthermore, research has revealed that the gas adsorption performance of two-dimensional (2D) MoSe₂ can be significantly enhanced through doping with transition metals [7,8]. Surface doping with elements such as Fe, Co, Ag, and Pt has been shown to improve the adsorption capacity of various materials [9]. For instance, Wang et al. investigated the gas sensing capabilities of Sc, Ti, Cr, and Mn-doped MoS₂ for phenol and N₂H₄ detection [10], while Chettri et al. studied the adsorption behavior of Fe-doped MoS₂ toward CH₄N₂O and CH₃OH molecules [11]. In the present study, Cu doping in 2D MoSe₂ is explored to enhance its gas adsorption efficiency, specifically for NH₃ molecules. To understand the underlying mechanisms, first-principles calculations based on DFT are employed. For structural stability, Cu atoms are substituted at Se sites in the MoSe₂ lattice, and the corresponding formation energy is calculated. The investigation includes determining the most favorable adsorption site for the NH₃ molecule on the monolayer, followed by calculations of adsorption energy, charge transfer, and electronic band structure before and after doping. This theoretical analysis provides insight into how Cu doping enhances the gas-sensing performance of 2D MoSe₂, offering valuable guidance for designing efficient gas sensor materials.

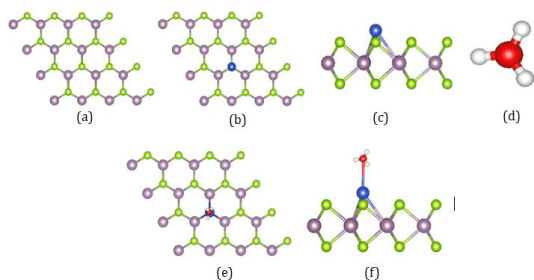


Figure 1 (a) MoSe₂ (b) Cu-MoSe₂ (Top View) (c) Cu-MoSe₂ (Side View) (d) NH₃ Gas Molecule (e) NH₃ adsorbed Cu-MoSe₂ (Top View) (f) NH₃ adsorbed Cu-MoSe₂ (Side View), (Mo-Indigo, Se- Green, Cu- Blur, N- Red, H-White)

II. METHODS

To evaluate the adsorption capability of the MoSe₂ monolayer (ML), a 4×4×1 supercell structure was constructed with a vacuum spacing of 15 Å perpendicular to the ML (z-axis) to prevent interlayer interactions. The optimized lattice constant of MoSe₂ was determined to be 3.31 Å, which aligns well with previously reported values [12]. Electronic and adsorption characteristics were computed using the SIESTA simulation package, employing an optimized configuration of the adsorbed SO₂ molecule [13]. A double-zeta polarized (DZP) basis set was applied to ensure an accurate representation of atomic orbitals, along with the generalized gradient approximation (GGA) using the Perdew–Burke–Ernzerhof (PBE) functional for exchange-correlation interactions [41,15]. The force and energy convergence criteria were set to 0.01 eV/Å and 10⁻⁵ eV, respectively. A mesh cutoff energy of 650 eV was used, and Brillouin zone sampling was performed using an 8×8×1 Monkhorst-Pack k-point grid for the structural relaxation of the MoSe₂ monolayer [16]. Charge transfer between the SO₂ molecule and the MoSe₂ surface was quantified using Mulliken population analysis [17]. Additionally, Cu: 3d10 4s1, Mo: 4d5 5s1, and Se: 4s2 4p4 were used for investigating NH₃ adsorption on Cu doped MoSe₂.

III. RESULTS AND DISCUSSION

A. Structure optimization of MoSe₂ and Cu-doped MoSe₂

Figure 1(a) shows the optimized structure of pristine MoSe₂, where each molybdenum (Mo) atom makes bonds with neighboring selenium (Se) atoms at a bond length of 2.504 Å. The Se–Mo–Se and Mo–Se–Mo bond angles are approximately 82.7°, aligning well with previously reported data [18]. The Mo–Mo and Se–Se interatomic distances are 3.314 Å and 3.317 Å, respectively (with an alternate Se–Se distance of 3.231 Å in another direction), and the Mo–Se bond measures approximately 2.505 Å. These structural parameters are in good agreement with earlier studies [18].

The electronic properties of pristine MoSe₂ were also calculated, revealing a direct bandgap of 1.40 eV, which is consistent with values reported in the literature [19]. Prior studies suggest that Cu atoms suitable to be positioned on Se sites during doping [20]. Based on this, Cu substitutional doping was performed by replacing a Se atom in the optimized 4×4×1 MoSe₂ supercell. The doped Cu atom forms stable bonds with three adjacent Mo atoms at distances of 4.096 Å, 4.097 Å, and 4.098 Å, slightly sticking out ~2 Å above the Se atomic plane due to its relatively larger atomic radius.

To measure the structural stability of both pristine and Cu-doped systems, formation energy (E_f) and binding energy (E_b) were calculated using equations (1) and (2), resulting values of -6.62 and -4.78 eV, respectively. These negative values authorize the thermodynamic stability of the Cu-doped MoSe₂ system with a Se vacancy, consistent with previous findings [21,22].

$$E_f = \frac{1}{N} [E_{\text{MoSe}_2} - xE_{\text{Mo}} - yE_{\text{Se}}] \quad (1)$$

$$E_b = E_{\text{Cu-MoSe}_2} - E_{\text{Cu}} - E_{\text{vac}} \quad (2)$$

In equation (1), the terms E_{Mo} and E_{Se} represent the energy of isolated Mo and Se atoms, respectively, while $E_{\text{(MoSe}_2\text{)}}$ denote the ground-state energy of MoSe₂. In equation (2), $E_{\text{(Cu-MoSe}_2\text{)}}$ indicates the energy of the Cu doped MoSe₂, where E_{Cu} and E_{vac} stand for the total energy of individual Cu and undoped MoSe₂ with Se vacancy on the ML. x and y

show the numbers of Mo and Se atoms, respectively, and N represents entire number of atoms in MoSe₂. Additionally, examined the interaction between a single metal atom and MoSe₂. It was obtained that there is a charge transfer from the Cu atom to the ML MoSe₂ of 0.23e, which is likely crucial for the chemical activity and sensitivity of the doped ML MoSe₂. To further explore the effects introduced by doping metal atoms into defective MoSe₂, the research conducted additional investigations on the band gap of Cu-doped MoSe₂, revealing a decrease.

B. Adsorption properties MoSe₂ and Cu-doped MoSe₂ system

In this study, the Cu-doped MoSe₂ gas detection performance mechanism with NH₃ gas molecule, it is computed the adsorption energy of the surface for both systems (undoped and doped). The strength of gas molecule adsorption on the surface of 2-D MoSe₂ is indicated by the adsorption energy value, which is defined as follows:

$$E_{\text{ads}} = E_{\text{Cu-MoSe}_2+\text{Gas}} - E_{\text{Cu-MoSe}_2} - E_{\text{Gas}} \quad (3)$$

Where $E_{\text{(Cu-MoSe}_2+\text{Gas)}}$ represents the total energy of NH₃ absorbed Cu-MoSe₂, and E_{Gas} denotes the energy of isolated NH₃. The greater negative value of the adsorption energy, the more vigorous the gas molecule's attachment to the substrate [23]. The adsorption energy of 2-D MoSe₂ for NH₃ before adding Cu-atom is lower than -0.5 eV, as indicated in Table1, suggesting physical adsorption. The adsorption energy does, however, approach -1eV following doping, indicating that Cu doping does, in fact, improve the 2-D MoSe₂'s ability to adsorb gas molecule and, consequently, the electron interaction between gas molecule and MoSe₂.

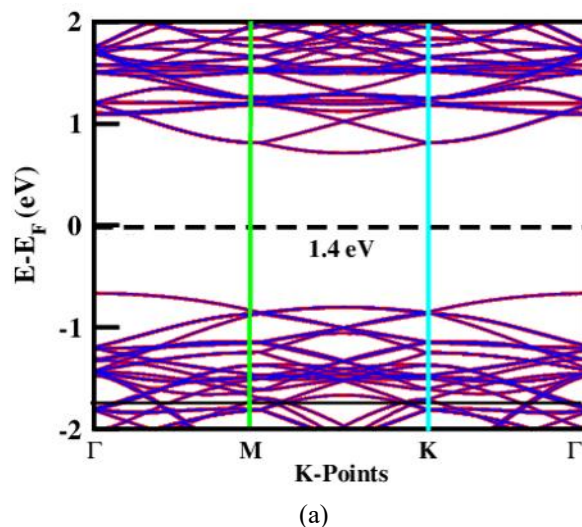
Table 1 Calculated parameters of undoped MoSe₂ and Cu-MoSe₂ adsorption structure.

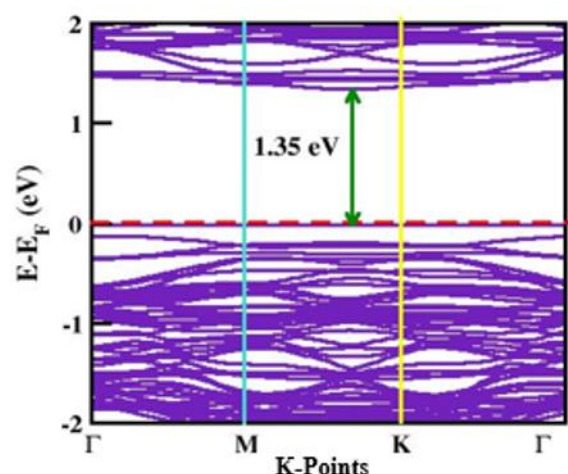
Monolayers	E_{ads} (eV)	Q_t (e)
NH ₃ /MoSe ₂	-0.46	0.09e
NH ₃ /Cu-MoSe ₂	-1.42	-0.19e

C. Electronic properties MoSe₂ and Cu-doped MoSe₂ system

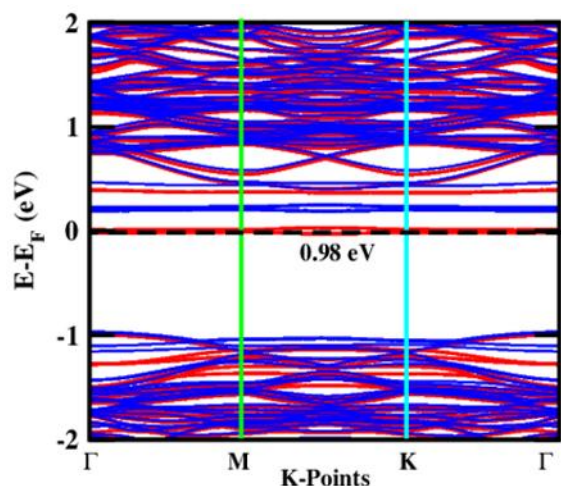
In MoSe₂ ML, it is observed that there is a no energy level region near the Fermi level (shifted to zero), indicating semiconducting behavior, as shown in Figure 2(a). However, after Cu doping, impurity states are introduced into the system, altering the region near the Fermi level, as depicted in Figure 2(c). These impurity-induced states contribute to changes in the electronic structure, enhancing conductivity of the Cu-doped MoSe₂ ML and bandgap reduces to 0.98 eV. All the estimated value of bandgaps for both systems are close agreement with the published work [24,22].

The adsorption of gas molecules onto the Cu-doped MoSe₂ monolayer (ML) significantly influences its gas sensing performance. The interaction with NH₃ molecules modifies the electronic band structure of the Cu-MoSe₂ ML, resulting in a reduced bandgap of 0.72 eV. This reduction suggests an enhancement in electrical conductivity upon gas adsorption. Figure 2 presents (BS), highlighting the effects of NH₃ adsorption on both undoped and Cu-doped MoSe₂ MLs.

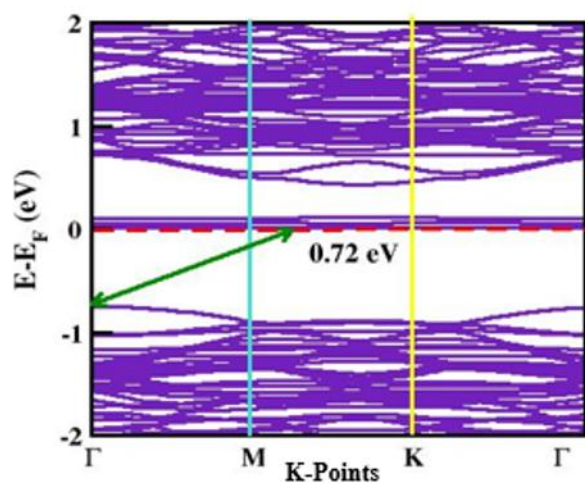




(b)



(c)



(d)

Figure 2 Bandstructure of (a) MoSe2 (b) NH3 adsorbed MoSe2(c) Cu-MoSe2 (d) NH3 adsorbed Cu-MoSe2

D. Exploring Sensors Based on Resistance Characteristics

When gas adsorption (NH₃) is introduced to the Cu-doped MoSe₂ ML, the band structure of the MoSe₂ ML is modulated, which further changes the conductivity (σ). Equations 5 and 6 [25], which are provided below, are used to empirically estimate the change in electronic conductivity and sensitivity:

$$\sigma = \lambda e^{\frac{-E_g}{2k_B T}} \quad (4)$$

$$S = \frac{1/\sigma_{Gas} - 1/\sigma_{pure}}{1/\sigma_{pure}} \quad (5)$$

Here, λ constant, k_B is the Boltzmann constant, and T is the temperature in K. The relationship between bandgap and conductivity is inverse. In our study, the bandgap of the Cu-MoSe₂ reduces to 0.72 eV during NH₃ adsorption. The results indicate that Cu doping markedly enhances the NH₃ sensing performance of MoSe₂, increasing its sensitivity from 62.36% to 99.37%. These significant changes in conductivity of the Cu-MoSe₂ ML demonstrate the material's potential as a liable resistance-type gas sensor for NH₃ detection through the use of a resistance detection-based apparatus.

Table 2 Calculated Bandgap and sensitivity of undoped MoSe₂ and Cu-MoSe₂ adsorption structure.

Monolayers	Bandgap (eV)	Sensitivity (%)
MoSe ₂	1.4	-
Cu-MoSe ₂	0.98	62.36
NH ₃ /MoSe ₂	1.35	-
NH ₃ /Cu-MoSe ₂	0.72	99.37

E. Recovery Time

This section reports the desorption ability of Cu-MoSe₂ ML towards NH₃ in terms of recovery time (τ). The Arrhenius equation and transition state theory serve as the foundation to estimate recovery time [26].

$$\tau = A e^{-\frac{E_a}{k_B T}} \quad (6)$$

A is known as attempt frequency, taken 10-12 s⁻¹ according to previous reports [22]. A number of factors, such as temperature (T) and Ea (magnitude of the same as Eads), can affect the recovery time in desorption processes. Gas desorption would be more difficult at higher Eads, and this process can be efficiently accelerated by raising the temperature. The recovery time for the desorption of gas at different temperatures was calculated using the Ea values (as stated in table 3). It may be concluded that at room temperature, NH₃ desorption from the Cu-MoSe₂ ML would be quite simple. The desorption time from the ML reduces with increasing temperature. As a result, using Cu-MoSe₂ ML as the sensing material for NH₃ detection would be suitable since gas sensors would function effectively.

Table 3 Recovery time of NH₃ gas molecule on Cu-MoSe₂ as a function of temperature

ML	Temperature (in K)	Recovery Time (in sec)
NH ₃ /Cu-MoSe ₂	298	3.34×10^{10}
	398	5.78×10^4
	498	26.59

IV. CONCLUSION

This paper investigated the adsorption of NH₃ gas molecules on a Cu-doped MoSe₂ monolayer using the SIESTA under the DFT relationships. Using the theoretical simulation, the adsorption energy, bandgap, recovery time, total charge transfer, and sensitivity were all investigated. The adsorption characteristics of the Cu-MoSe₂ monolayer were improved, according to the results. Because of the high adsorption energy, the NH₃ molecules and Cu-MoSe₂ have a tight bond. The conductivity of the bandgap increases significantly after Cu doping and NH₃ molecule adsorption.

The magnetic behaviour was seen after doping of Cu atom in the MoSe₂ ML. Furthermore, the Cu-MoSe₂ monolayer has an outstanding sensitivity of 99.37% for adsorbing NH₃ molecules. The NH₃ configuration was shown to have a shorter desorption time of 26.59s at 498K, which reduced as the temperature rise. For a resistance-type sensor that can detect NH₃ molecule, Cu-MoSe₂ monolayer is a practicable choice.

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